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Memristive devices with a large memory margin based on nanocrystalline organic-inorganic hybrid $\text{CH}_3\text{NH}_3\text{PbBr}_3$ perovskite active layer

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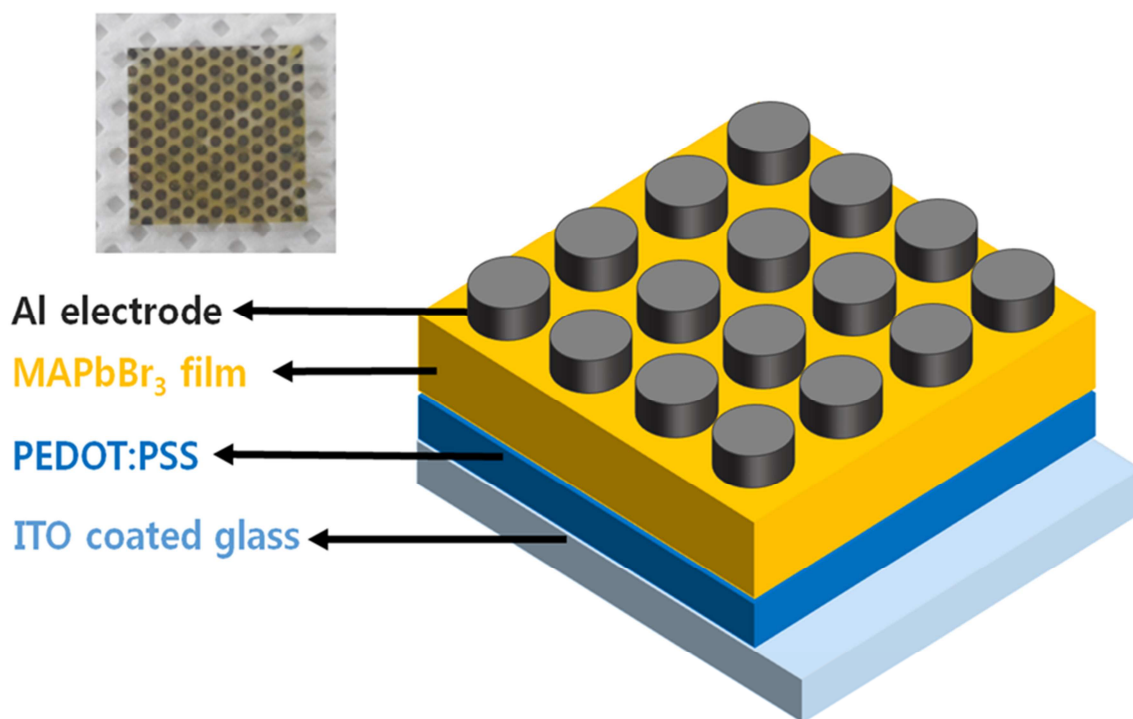
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